



# HAD826SP

NPN EPITAXIAL PLANAR TRANSISTOR

## Description

The HAD826SP is designed for general purpose amplifier and high speed, medium-power switching applications.

## Features

- Low Collector Saturation Voltage
- High Speed Switching

## Absolute Maximum Ratings

- Maximum Temperatures  
 Storage Temperature..... -55 ~ +150 °C  
 Junction Temperature..... 150 °C Maximum
- Maximum Power Dissipation  
 Total Power Dissipation (Ta=25°C)..... 500 mW
- Maximum Voltages and Currents (Ta=25°C)  
 VCBO Collector to Base Voltage..... 75 V  
 VCEO Collector to Emitter Voltage ..... 40 V  
 VEBO Emitter to Base Voltage ..... 6 V  
 IC Collector Current ..... 500 mA

## Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	75	-	-	V	IC=10uA, IE=0
BVCEO	40	-	-	V	IC=10mA, IB=0
BVEBO	6	-	-	V	IE=10uA, IC=0
ICBO	-	-	10	nA	VCB=60V, IE=0
ICEX	-	-	10	nA	VCB=60V, VEB(OFF)=3V
IEBO	-	-	50	nA	VEB=3V, IC=0
*VCE(sat)1	-	-	300	mv	IC=150mA, IB=15mA
*VCE(sat)2	-	-	1	V	IC=500mA, IB=50mA
*VBE(sat)1	-	-	1.2	V	IC=150mA, IB=15mA
*VBE(sat)2	-	-	2	V	IC=500mA, IB=50mA
*hFE1	35	-	-		VCE=10V, IC=100uA
*hFE2	50	-	-		VCE=10V, IC=1mA
*hFE3	75	-	-		VCE=10V, IC=10mA
*hFE4	100	-	300		VCE=10V, IC=150mA
*hFE5	40	-	-		VCE=10V, IC=500mA
*hFE6	50	-	-		VCE=1V, IC=150mA
fT	300	-	-	MHz	VCE=20V, IC=20mA, f =100MHz
Cob	-	-	8	pF	VCB=10V, f=1MHz

\*Pulse Test : Pulse Width ≤380us, Duty Cycle≤2%



### Characteristics Curve

